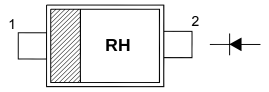
SDB720WS

SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

for high frequency rectification

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



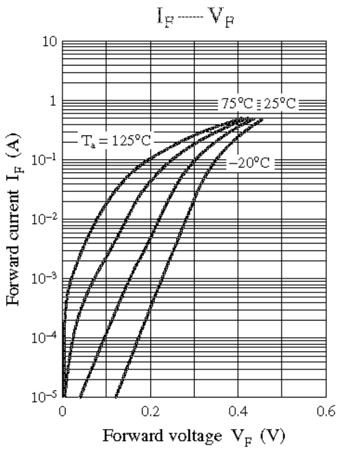
Top View
Marking Code: "**RH**"
Simplified outline SOD-323 and symbol

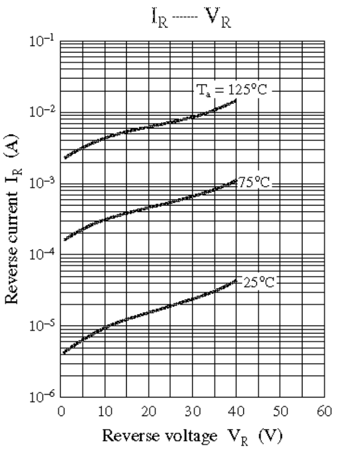
Absolute Maximum Ratings (T_a = 25 °C)

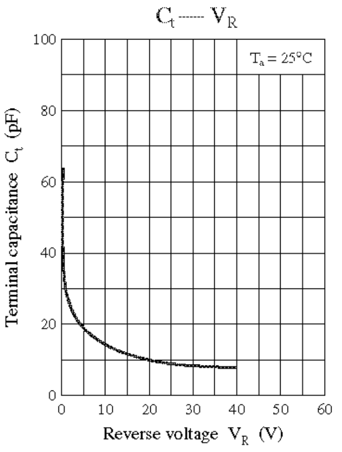
Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	40	V
Reverse Voltage	V_R	40	V
Average Forward Current	I_O	0.5	A
Non-repetitive Peak Forward Surge Current	I_{FSM}	2	A
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	- 55 to + 150	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at I_F = 500 mA	V_F	-	0.55	V
Reverse Current at V_R = 35 V	I_R	-	100	µA
Terminal Capacitance at V_R = 0 V, f = 1 MHz	C_T	60	-	pF
Reverse Recovery Time at I_F = I_R = 100 mA, I_{rr} = 10 mA, R_L = 100 Ω	t_{rr}	5	-	nS



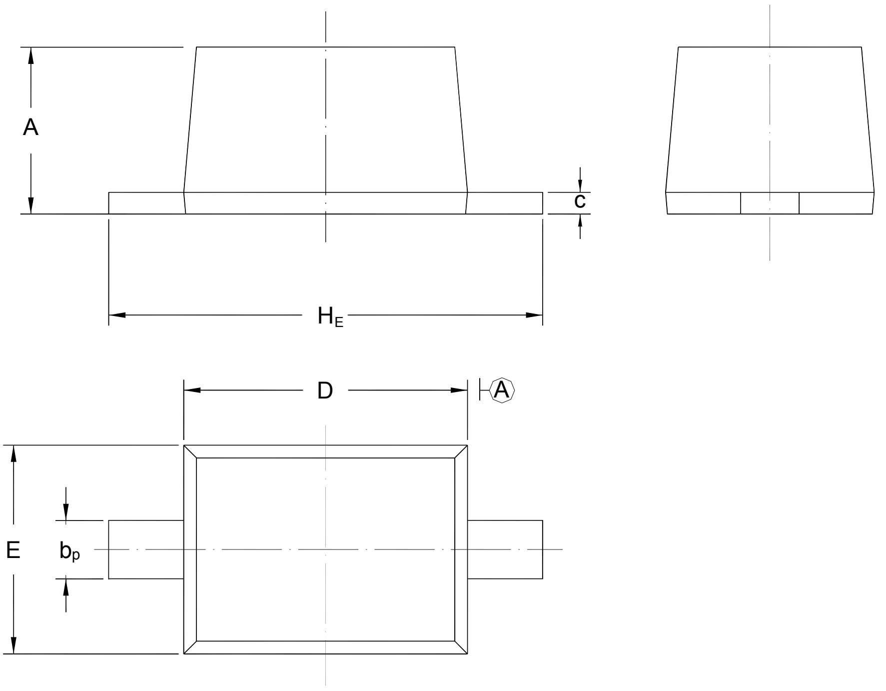




Dated : 16/01/2007

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads **SOD-323**



UNIT	A	b_p	C	D	E	H_E
mm	1.10 0.80	0.40 0.25	0.15 0.10	1.80 1.60	1.35 1.15	2.80 2.30